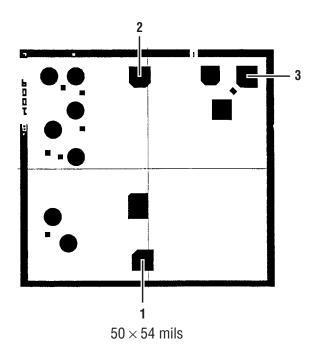


RH1009 2.5V Reference



DIE CROSS REFERENCE

LTC Finished	Order DICE CANDIDATE
Part Number	Part Number Below
RH1009	RH1009 DICE
RH1009	RH1009 DWF

PAD FUNCTION

- 1. V+
- 2. ADJ
- 3. V⁻

NOTE: CONNECT SUBSTRATE TO V-

DICE ELECTRICAL TEST LIMITS

$T_J = 25^{\circ}C$. Preirradiation

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
V_{Z}	Reverse Breakdown Voltage	I _R = 1mA	2.495	2.505	V
$\frac{\Delta V_{Z}}{\Delta I_{R}}$	Reverse Breakdown Voltage Change with Current	$400\mu\text{A} \le I_{\text{R}} \le 10\text{mA}$		6	mV



DICE SPECIFICATION

RH1009

Wafer level testing is performed per the indicated specifications for dice. Considerable differences in performance can often be observed for dice versus packaged units due to the influences of packaging and assembly on certain devices and/or parameters. Please consult factory for more information on dice performance and lot qualifications via lot sampling test procedures.

Dice data sheet subject to change. Please consult factory for current revision in production.

I.D.No. 66-13-1009